

# SILICON TRANSISTOR 2SB1475

### PNP SILICON EPITAXIAL TRANSISTOR **AUDIO FREQUENCY AMPLIFIER**

#### **DESCRIPTION**

2SB1475 is designed for audio frequency amplifier and switching application, especially in VCR cameras and headphone stereos.

## PACKAGE DIMENSIONS in millimeters $2.1\pm0.1$ $1.25 \pm 0.1$ 3 Marking 0 to 0.1 1. Emitter 2. Base 3. Collector

#### **FEATURES**

- Super Miniature Package
- High DC Current  $I_{C(DC)}$  = -500 mA MAX. Low  $V_{CE(sat)} \cdot V_{CE(sat)}$  = -60 mV at -100 mA

#### **QUALITY GRADE**

Standard

Please refer to "Quality grade on NEC Semiconductor Devices" (Document number IEI-1209) published by NEC Corporation to know the specification of quality grade on the devices and its recommended applications.

#### **ABSOLUTE MAXIMUM RATINGS**

Maximum Voltages and Current (Ta = 2	25 °C)		•
Collector to Base Voltage	$V_{\sf CBO}$	<b>–25</b>	V
Collector to Emitter Voltage	$V_{CEO}$	-16	V
Emitter to Base Voltage	$V_{EBO}$	6	V <sub>.</sub>
Collector Current (DC)	Ι <sub>C</sub>	-500	mΑ
Maximum Power Dissipation			
Total Power Dissipation			
at 25 °C Ambient Temperature	$P_T$	150	mW .
Maximum Temperatures			0 -
Junction Temperature	Τį	150	o° O°
Storage Temperature Range	$T_{sta}$	-55 to +150	°C

#### ELECTRICAL CHARACTERISTICS (Ta = 25 °C)

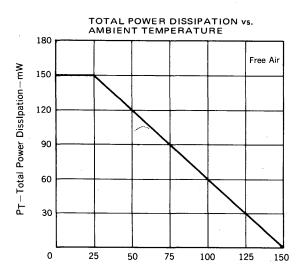
PARAMETER	SYMBOL	MIN.	TYP.	MAX.	UNIT	TEST CONDITIONS
Collector Cutoff Current	ІСВО			-100	nA	V <sub>CB</sub> = -16 V, I <sub>E</sub> = 0
Emitter Cutoff Current	I <sub>EBO</sub>			-100	nA	V <sub>EB</sub> = -6.0 V, I <sub>C</sub> = 0
DC Current Gain	hFE1 *	110	200	400	_	$V_{CE} = -1.0 \text{ V}, I_{C} = -100 \text{ mA}$
DC Current Gain	hFE2 *	100			_	$V_{CE} = -1.0 \text{ V}, I_{C} = -500 \text{ mA}$
Collector Saturation Voltage	V <sub>CE(sat1)</sub> *		-60	-120	mV.	I <sub>C</sub> = -100 mA, I <sub>B</sub> = -10 mA
Collector Saturation Voltage	VCE(sat2) *		-250	-400	mV	$I_C = -500 \text{ mA}, I_B = -20 \text{ mA}$
Base Saturation Voltage	V <sub>BE(sat)</sub> *		-0.95	-1.2	V	I <sub>C</sub> = -2.0 A, I <sub>B</sub> = -0.1 A
Base to Emitter Voltage	V <sub>BE</sub> *	-0.6	-0.66	-0.7	V	$V_{CE} = -1.0 \text{ V}, I_{C} = -10 \text{ mA}$
Gain Bandwidth Product	f <sub>T</sub>	50			MHz	$V_{CE} = -3.0 \text{ V, } I_{E} = 100 \text{ mA}$
Output Capacitance	C <sub>ob</sub>			15	pF	V <sub>CB</sub> = -10 V, I <sub>E</sub> = 0, f = 1.0 M

<sup>\*</sup> Pulsed: PW ≤ 350 µs, Duty Cycle ≤ 2 %

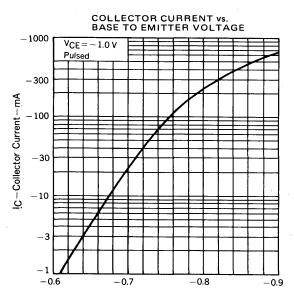
#### h<sub>FE</sub> Classification

MARKING	B42	B43	B44	
hFE	110 to 240	190 to 320	270 to 400	

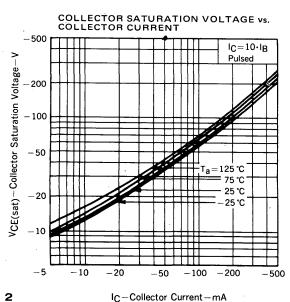
### TYPICAL CHARACTERISTICS (Ta = 25 °C)



Ta-Ambient Temperature-°C



VBE-Base to Emitter Voltage-V



COLLECTOR CURRENT vs.
COLLECTOR TO EMITTER VOLTAGE -50200 μΑ Pulsed -40-Collector Current - mA 150 µA -30 -100 μA -20 ن  $I_B = -50 \mu A$ -10

VCE-Collector to Emitter Voltage-V

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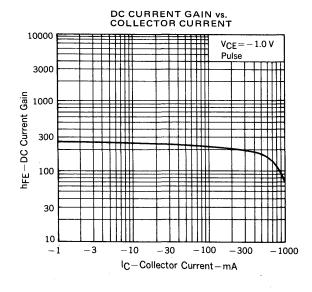
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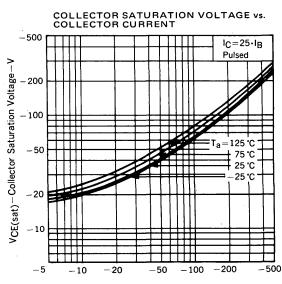
-10

-4

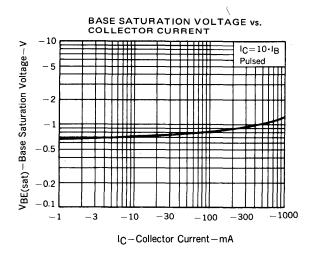
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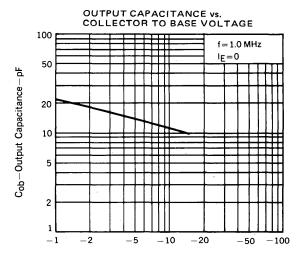
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IC-Collector Current-mA





VCB-Collector to Base Voltage-V

#### RECOMMENDED SOLDERING CONDITIONS

Mounting of this product by soldering should be done under the following conditions.

Please consult our representatives about soldering methods and conditions other than these.

#### SURFACE MOUNT TYPE

For details of the recommended soldering conditions, see the information document "SMT MANUAL" (IEI-1207).

Soldering Method	Soldering Conditions	Symbol for Recommended Conditions	
Infrared Reflow	Package peak temp.: 230 °C Soldering time: within 30 sec (above 210 °C) Soldering times: 1, Days limitation: none*	IR30-00	
Vapor Phase Soldering	Package peak temp.: 215 °C Soldering time: within 40 sec (above 200 °C) Soldering times: 1, Days limitation: none*	VP15-00	
Wave Soldering	Soldering bath temp.: below 260 °C Soldering time: within 10 sec Soldering times: 1, Days limitation: none*	ws60-00	

<sup>\*:</sup> Stored days under storage conditions at 25 °C and below 65 % R.H. after the dry-pack has been opened.

Note 1 Combination of soldering methods should be avoided.

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Application examples recommended by NEC Corporation

Standard: Data processing and office equipment, Communication equipment (terminal, mobile). Test and

Measurement equipment, Audio and Video equipment, Other consumer products, etc.

Special: Automotive and Transportation equipment, Communication equipment (trunk line), Train and

Traffic control devices, industrial robots, Burning control systems, antidisaster systems, anticrime

systems etc.